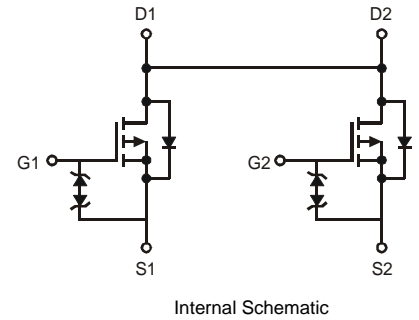
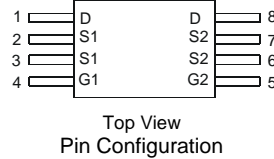
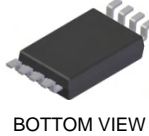


Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **ESD Protected up to 3kV**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: TSSOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.039 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	6.04	A
		$T_A = 85^\circ\text{C}$		3.96	
Pulsed Drain Current (Note 4)			I_{DM}	22	A

Thermal Characteristics

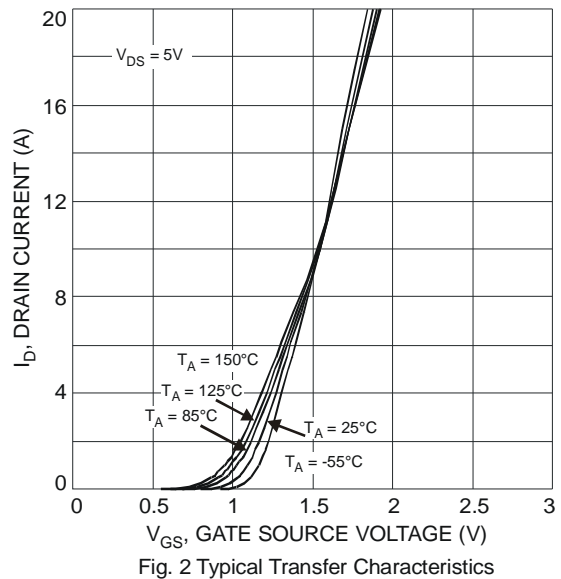
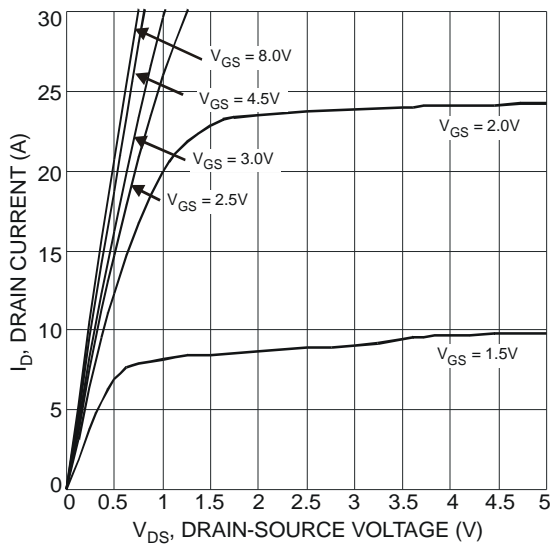
Characteristic			Symbol	Value	Unit
Power Dissipation (Note 3)			P_D	0.89	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$			$R_{\theta JA}$	142.7	$^\circ\text{C/W}$
Operating and Storage Temperature Range			T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 substrate PC board with minimum recommended pad layout.
 4. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.4	-0.7	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	23	35	m Ω	$V_{GS} = -4.5V, I_D = -4.0A$
		-	30	45		$V_{GS} = -2.5V, I_D = -4.0A$
		-	41	62		$V_{GS} = -1.8V, I_D = -2.0A$
Forward Transfer Admittance	$ Y_{fs} $	-	14	-	S	$V_{DS} = -5V, I_D = -4A$
Diodes Forward Voltage	V_{SD}	-	-0.7	-1.0	V	$I_S = -1A, V_{GS} = 0V$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	-	1610	-	pF	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	-	157	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	145	-	pF	
Gate Resistance	R_g	-	9.45	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_g	-	15.4	-	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_D = -4A$
Gate-Source Charge	Q_{gs}	-	2.5	-	nC	
Gate-Drain Charge	Q_{gd}	-	3.3	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	16.8	-	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$ $R_L = 10\Omega, R_G = 6.0\Omega, I_D = -1A$
Turn-On Rise Time	t_r	-	12.4	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	94.1	-	ns	
Turn-Off Fall Time	t_f	-	42.4	-	ns	

- Notes: 5. Short duration pulse test used to minimize self-heating effects.
6. Guaranteed by design. Not subject to production testing.



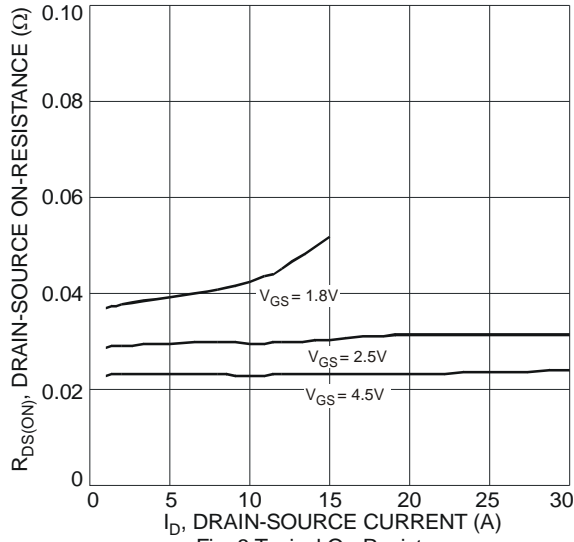


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

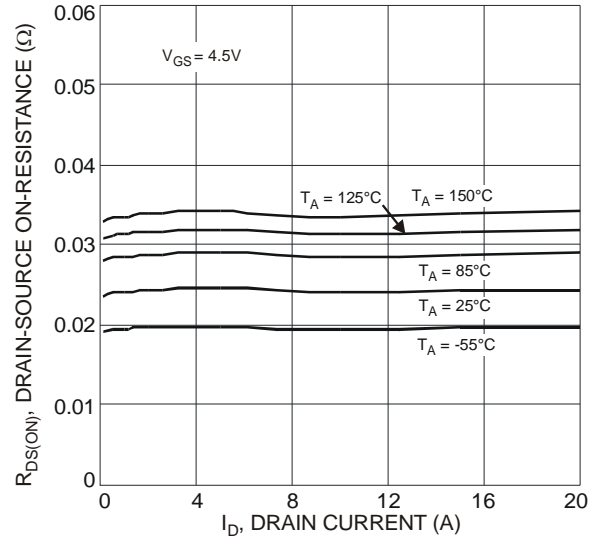


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

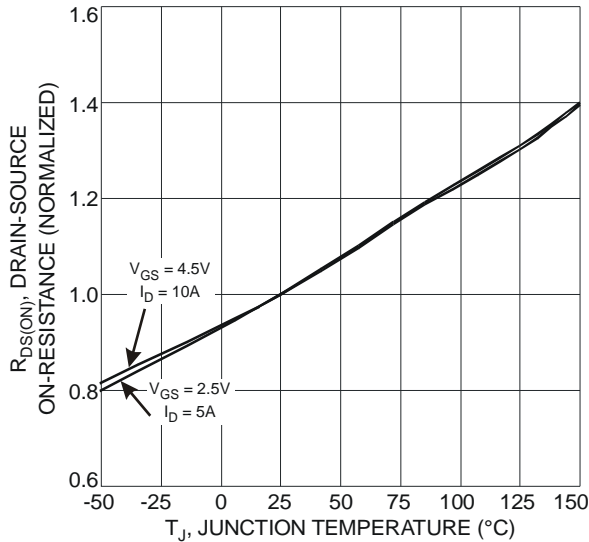


Fig. 5 On-Resistance Variation with Temperature

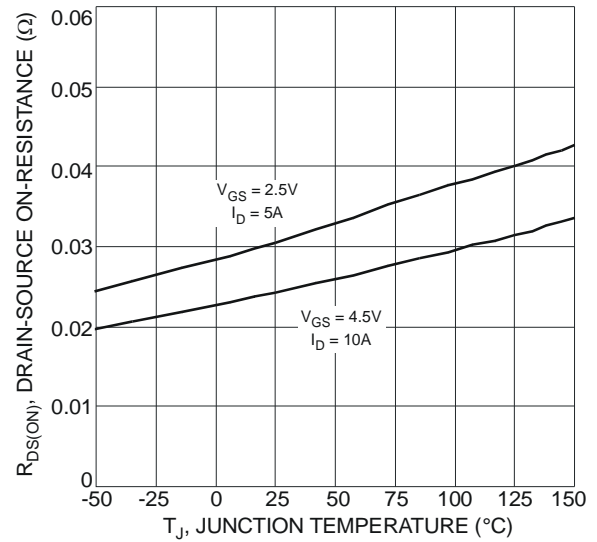


Fig. 6 On-Resistance Variation with Temperature

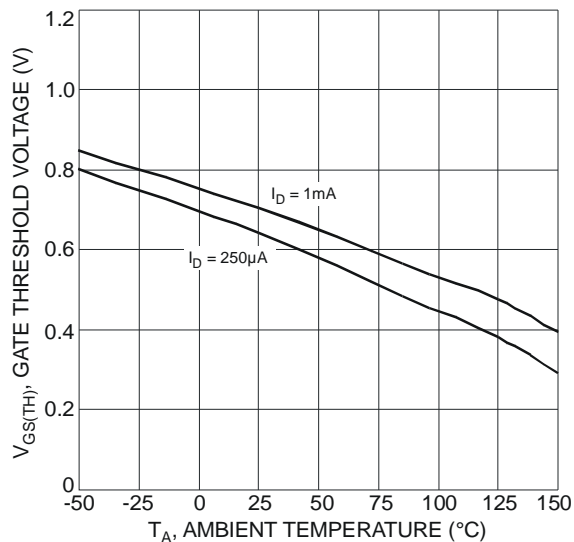


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

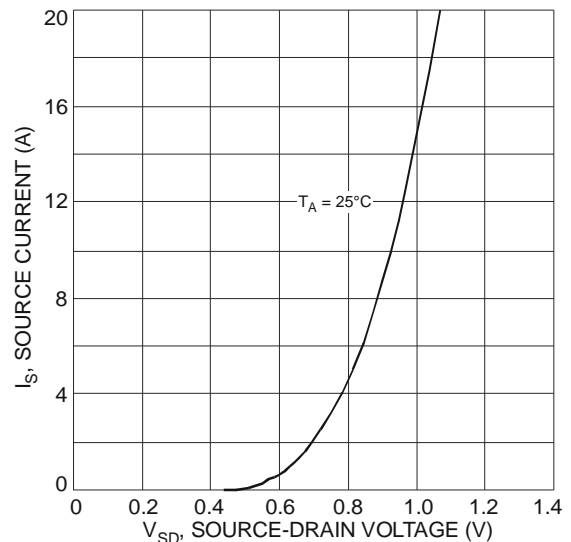


Fig. 8 Diode Forward Voltage vs. Current

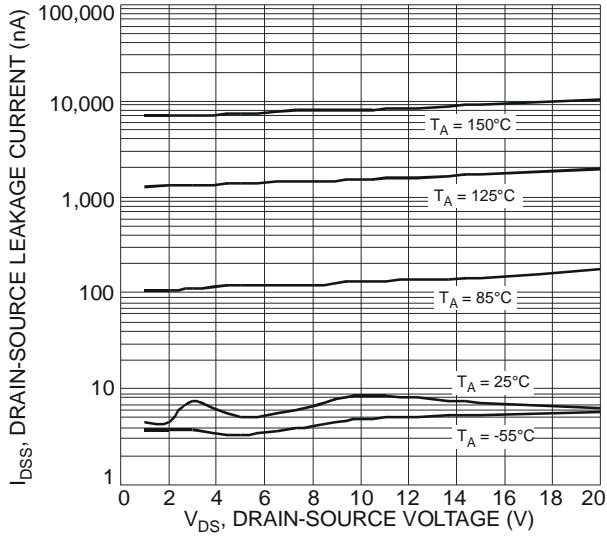


Fig. 9 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

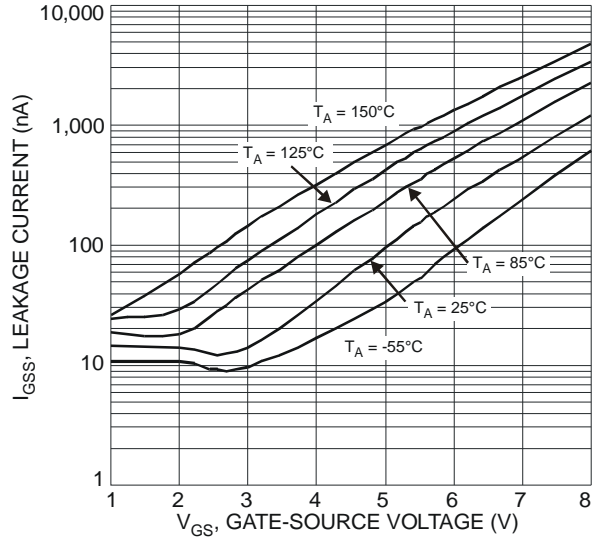


Fig. 10 Leakage Current vs. Gate-Source Voltage

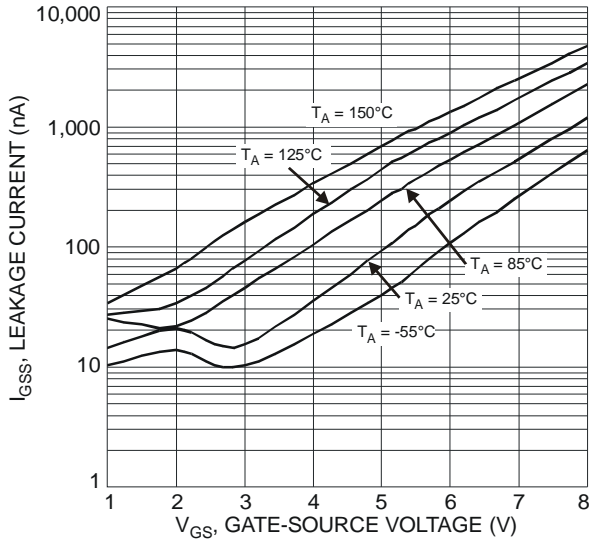


Fig. 11 Leakage Current vs. Gate-Source Voltage

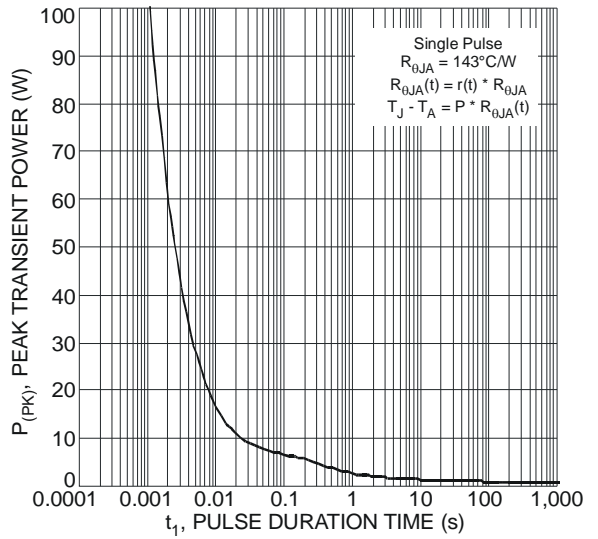


Fig. 12 Single Pulse Maximum Power Dissipation

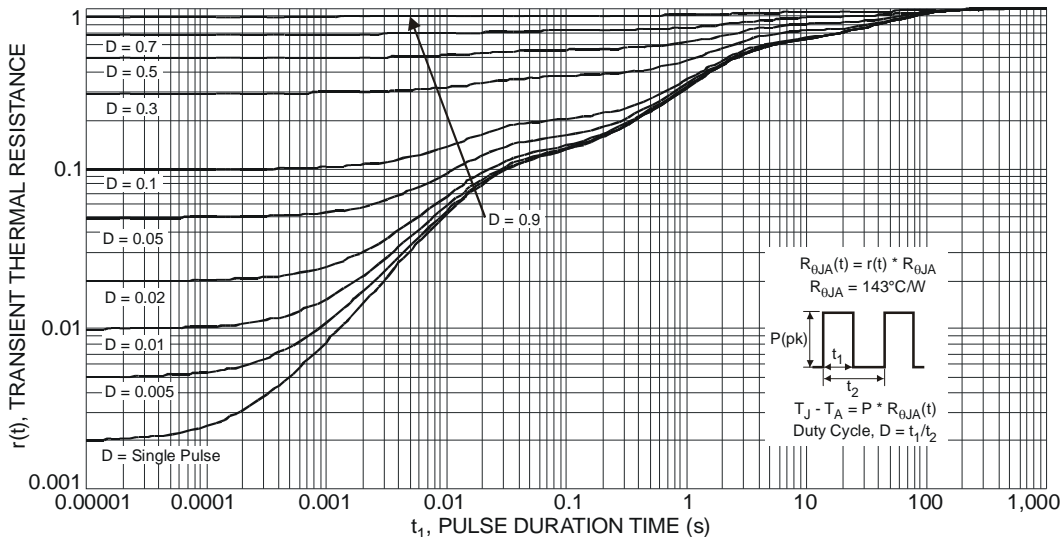


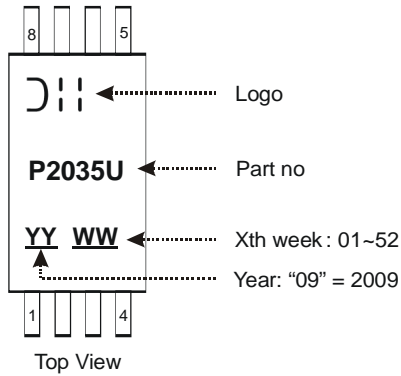
Fig. 13 Transient Thermal Response

Ordering Information (Note 7)

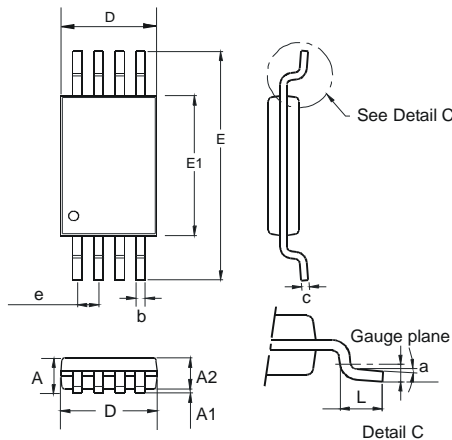
Part Number	Case	Packaging
DMP2035UTS-13	TSSOP-8L	2500 / Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

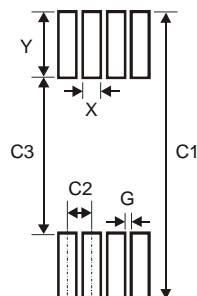


Package Outline Dimensions



TSSOP-8L			
Dim	Min	Max	Typ
a	0.09	-	-
A	-	1.20	-
A1	0.05	0.15	-
A2	0.825	1.025	0.925
b	0.19	0.30	-
c	0.09	0.20	-
D	2.90	3.10	3.025
e	-	-	0.65
E	-	-	6.40
E1	4.30	4.50	4.425
L	0.45	0.75	0.60
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20

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